

ABSTRACT OF THE DISCLOSURE

An aspect of a semiconductor device includes: a collector layer of first conductive type formed on a semiconductor substrate; a graft base layer of second conductive type formed in a surface region of the collector layer; a first base leading-out region of second conductive type formed on the graft base layer; a second base leading-out region of second conductive type formed on an upper surface and a side surface of the first base leading-out region; a base layer of second conductive type formed on the collector layer; an emitter layer of first conductive type formed in a surface region of the base layer; and an emitter leading-out region formed on the emitter layer.